

RESEARCH ARTICLE

Thermo-electro-optic energy conversion using plasmonic island embedded silicon microring circuit

Montree Bunruangses¹ | Phichai Youplao²
 | Suphanchai Punthawanunt³ |
 Iraj Sadegh Amiri⁴  |
 Nithiroth Pornsuwancharoen^{5,6} |
 Preecha Yupapin^{5,6} 

¹Department of Computer Engineering, Faculty of Industrial Education, Rajamangala University of Technology Phra Nakhon, Bangkok, Thailand

²Department of Electrical Engineering, Faculty of Industry and Technology, Rajamangala University of Technology Isan Sakon Nakhon Campus, Sakon Nakhon, Thailand

³Faculty of Science and Technology, Kasem Bundit University, Bangkok, Thailand

⁴Division of Materials Science and Engineering, Boston University, Boston, Massachusetts, USA

⁵Computational Optics Research Group, Advanced Institute of Materials Science, Ton Duc Thang University, District 7, Ho Chi Minh City, Vietnam

⁶Faculty of Applied Sciences, Ton Duc Thang University, District 7, Ho Chi Minh City, Vietnam

Correspondence

Preecha Yupapin, Faculty of Applied Sciences, Ton Duc Thang University, District 7, Ho Chi Minh City, Vietnam.
 Email: preecha.yupapin@tdtu.edu.vn

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Rajamangala University of Technology Phra Nakhon

Abstract

We propose the use of the thermo-electro-optic energy conversion system for daily sunlight charger. A circuit consists of a modified silicon microring circuit embedded by a plasmonic island at the center. The island materials consist of silicon-graphene-gold layers. The thermal expansion of the island materials from the daily sunlight can affect the change in island material lengths and transfer to the plasmon wave path difference, which can perform the energy conversion and a charger. In manipulation, the daily sunlight statistic from South East Asia, the significant daily charging mobility of $4.34 \times 10^{-6} \text{ cm}^2 \cdot (\text{V} \cdot \text{s})^{-1}/\text{Vs}$ with the input light

power of 10 mW can be obtained, which may be useful for one of the selected alternative energy sources.

KEYWORDS

microring circuit, microring resonator, plasmonic circuit, plasmonic island, thermo-electric circuit

1 | INTRODUCTION

Variant daily sunlight in nature is the powerful energy resource, which can be found in many applications,¹⁻⁵ especially for solar cell device input energy. However, the efficiency of such devices is still continuously improved.^{6,7} There is another way of an application when the heat from sunlight can be used to form the thermal devices,^{8,9} in which the direct thermal energy can be applied and the device functioned. Recently, the use of the variant sunlight for thermo-electric has shown a very interesting aspect, which can be used for an electrical device. In this article, we propose the use of the thermo-electro-optic energy conversion, in which the required output is the electron mobility that can be converted to be the required electrical output. By using the whispering gallery mode (WGM) output of the generated output beam, the reflected light intensity is given by $I_{\text{WGMR}} = -R_{\text{WGM}} I_{\text{WGMR}} \cdot R_{\text{WGM}}$ is the reflection output. Here, R_{WGM} is a coefficient of the reflection or the used material reflectivity.¹⁰

2 | BACKGROUND

In the manipulation, the input electric field, $E_{\text{in}} = E_z = E_0 e^{-ik_z z - \omega t + \varphi}$, is fed into the system along the z-axis direction with the wave propagation number k_z . E_0 represents the amplitude of the initial electric field, ω and φ represent the angular frequency and the phase of the propagation light, respectively.¹⁰

$$E_{\text{th}} = \sqrt{1-\gamma_1} \left(\sqrt{1-\kappa_1} E_{\text{in}} + j\sqrt{\kappa_1} E_4 e^{-\frac{\alpha L_D}{2} - jk_n \frac{L_D}{4}} \right) \quad (1)$$

$$E_{\text{dr}} = \sqrt{1-\gamma_3} \left(\sqrt{1-\kappa_3} E_{\text{add}} + j\sqrt{\kappa_3} E_2 e^{-\frac{\alpha L_D}{2} - jk_n \frac{L_D}{4}} \right) \quad (2)$$

$$E_{\text{out}} = \sqrt{1-\gamma_3} \left(\sqrt{1-\kappa_3} E_{\text{dr}}^* + j\sqrt{\kappa_3} E_2 e^{-\frac{\alpha L_D}{2} - jk_n \frac{L_D}{4}} \right) \quad (3)$$

$E_{\text{dr}}^* = -nE_{\text{dr}}$, where n is the ratio of the reflection, E_{out} represents the output electrical field that appears at the add

port. Each the electrical field that propagates within each part of the system represents by E_1, E_2, E_3, E_4, E_L , and E_R , illustrated as in Figure 1. The intensity insertion loss coefficients are 3 dB couplers, which is represents by γ_{is} , and κ_{is} are the coupling coefficients. The attenuation loss due to light propagates within the waveguide is α . The propagation constant is $k_n = \frac{2\pi}{\lambda} n_{\text{eff}}$.

The circumference of the island ring circumference is L_D , which is changed under the change with the daily variant temperature. The change in the linear dimension can be estimated to be $\Delta L_D/L_D = \alpha_L \Delta T$, where ΔL_D is the change in

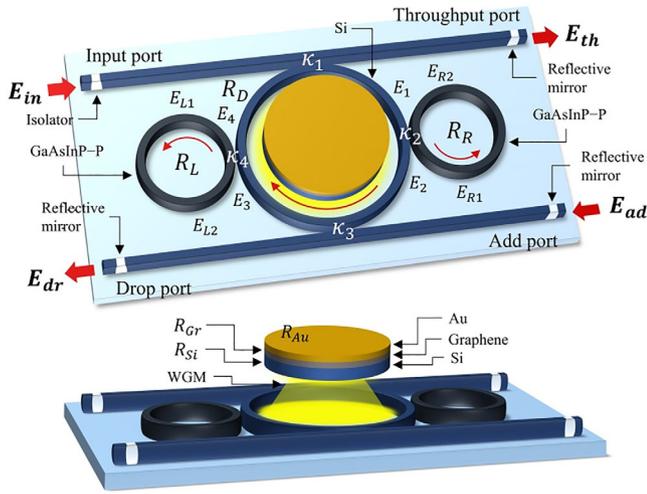


FIGURE 1 A microring circuit with the embedded plasmonic island at the centre ring, where R_L, R_R, R_D : the radius of the left, right, and centre ring, respectively. The coupling coefficients: $\kappa_s = 0.5$. R_{Au}, R_{Si}, R_{Gr} : the radius of Gold, Silicon, and Graphene plate, respectively. E_{in}, E_{th}, E_{dr} , and E_{ad} , represent the electrical fields of each port, throughput port, drop port, and add port, respectively [Color figure can be viewed at wileyonlinelibrary.com]

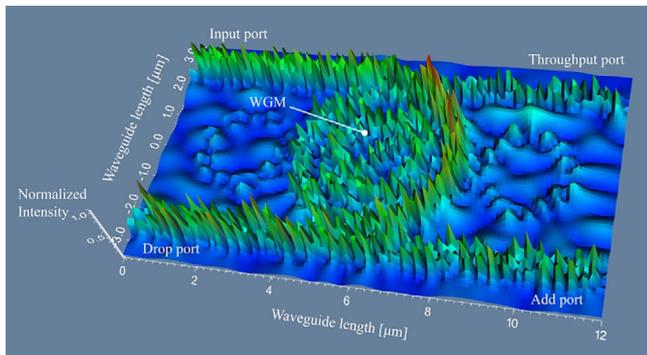


FIGURE 2 Graphical results obtained by the Optiwave program, where the used output is the whispering gallery mode (WGM) at the centre of the circuit as shown in Figure 1. The ring system, $R_L = R_R = 1.1 \mu\text{m}$, $R_D = 2.0 \mu\text{m}$, $\kappa_1 = \kappa_2 = \kappa_3 = \kappa_4 = 0.5$, $R_{Si} = R_{Au} = R_{Ga} = 1.6 \mu\text{m}$, of which the thickness: $0.1 \mu\text{m}$, $0.1 \mu\text{m}$, and $0.2 \mu\text{m}$, respectively, $n_{Si} = 3.47$. The input power is 10 mW with $1.55 \mu\text{m}$ center wavelength [Color figure can be viewed at wileyonlinelibrary.com]

the island ring circumference, α_L is the thermal expansion coefficient, ΔT is the change in temperature. However, the elongation limits of all materials are the applied conditions. The relation of the volume expansion coefficient as a function of the temperature can be evaluated by Grüneisen's equation,¹¹ which can express as Equations (4)-(8).¹²

$$\beta = \frac{1}{V} \left(\frac{\partial V}{\partial T} \right)_P \quad (4)$$

$$\beta = \frac{C_V}{Q_0 [1 - k(U/Q_0)]^2} \quad (5)$$

$$\frac{\Delta V}{V_0} = \beta \Delta T \quad (6)$$

where $\Delta V/V_0$ is the fractional change in volume, C_V is the capacity of molar heat considered at constant volume, U is

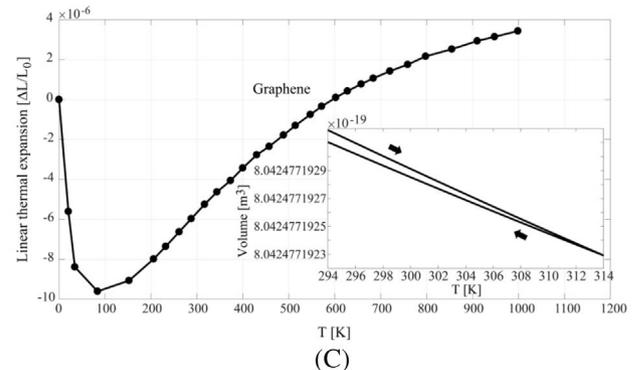
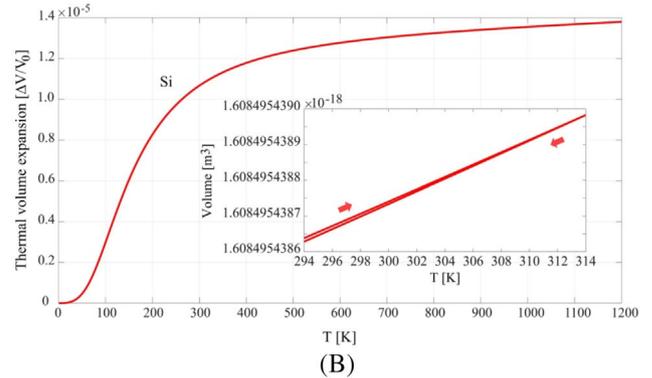
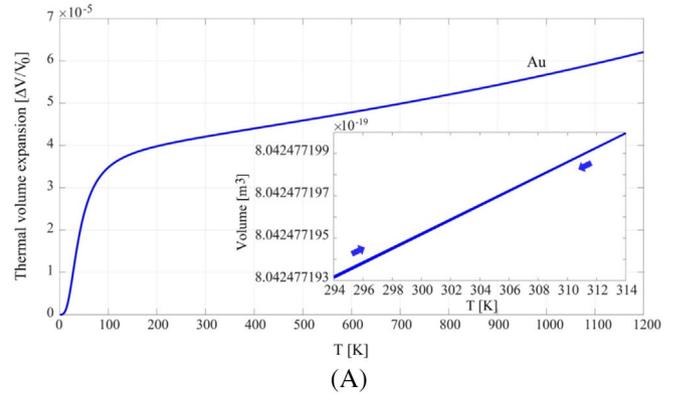


FIGURE 3 Thermal expansion of the island rings-silicon, graphene, gold, where A, and B,¹¹ C^{12,13} [Color figure can be viewed at wileyonlinelibrary.com]

TABLE 1 Specified parameters for charge-carrier number density evaluation¹⁶

	Density (g/cm ³)	Free electron number	Molar mass (g/mol)	Conductivity: σ (S/m)
Au	19.30	1	196.97	4.10×10^7

the lattice vibrations energy, Q_0 and k are constant quantities. Then, with a specified Debye temperature, θ_D , both C_V and U at any temperature T can be calculated by using Equations (7) and (8), where R is the molar gas constant.

$$C_V = 3R \left[12 \left(\frac{T}{\theta_D} \right)^3 \int_0^{\theta_D/T} \frac{x^3 dx}{e^x - 1} - 3 \frac{\theta_D/T}{e^{\theta_D/T} - 1} \right] \quad (7)$$

$$U = \int_0^T C_V dT \quad (8)$$

3 | SIMULATION RESULTS

By using the graphical program called an Optiwave program, from which the result of the WGM is obtained as shown in Figure 2, where the selected parameters of the system in Figure 1 were applied. The major role was the side ring radii that can be used to control to obtain the WGM output. From which the key effect was the nonlinear Kerr effect of the GaAsInP-P material. Those identified parameters will use for the MATLAB program later on. The used materials thermal characteristics are also are given in Figure 3, in which the fractional change in volume for Au and Si can be illustrated as in Figure 3A,B. In addition, for graphene, the fractional change in length can be considered from the theoretical data by References 13 and 14 and illustrated in Figure 3C. Based on the average temperature, according to statistics such as Bangkok, Thailand, which changes in the range of 20°C to 40°C ($\sim 294^\circ\text{K}$ - 314°Kelvin),¹⁵ the volume change of the island according to the type of material can be considered as follows. Figure diagram in each figure of Figure 3. The parameters are given by the following details. As the specified parameters used in Table 1, the charge-carrier number density for an Au island can be calculated by an Equation (8), which is $n = 5.8987 \times 10^{28}$ electrons. m^{-3} . The Au island radius $R_{Au} = 1.6 \mu\text{m}$, of which the thickness is 100 nm. Then the calculated charge-carrier is 4.7440×10^{10} electrons, where an electron charge, $e = 1.602 \times 10^{-19}$ coulombs. Thus, the island's maximum electrical charge is $Q_{\max} = 7.5999 \times 10^{-9}$ coulombs. Furthermore, the current density, $J = \sigma E$, where E represents the electric field inside the Au plate and its conductivity (σ) are related to the thickness of the plate (T_{Au}). The cross-sectional area of the Au island is $A = \pi[R_{Au}]^2$. Thus, the charging current can be considered as $I = JA = \sigma T_{Au} EA$ and results in the induced charge Q within the Au plate, which can be expressed by a function of time: t , as $Q = I \times t$. Therefore, the time-dependent charge on the Au

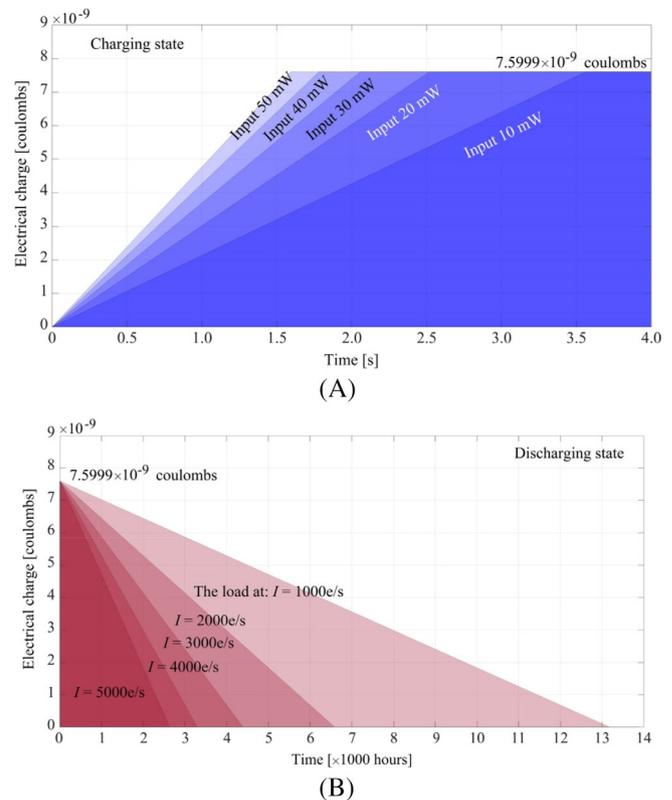


FIGURE 4 Results of the induced electrical charge characteristics using the proposed circuit, A, the charging state, where the input light powers are varied from 10 to 50 mW, and B, the discharging state, where the loads are varied from 1000 to 5000 e/s [Color figure can be viewed at wileyonlinelibrary.com]

plate within the plasmonic island can be expressed by $Q(t) = [\sigma T_{Au} EA \times t]$. This time-dependent charging Q can be illustrated as shown in Figure 4A, in which the discharging state will depend on the applied loads. For simplification, it starts from the maximum charge, Q_{\max} , on the plasmonic island and the load draws the current as an electrons source, an amount of electrons/s (Q/s). Thus, the time-dependent discharging Q can be considered as $Q(t) = [Q_{\max} - met]$, which is illustrated in Figure 4B, where m is an amount of discharging in electrons/s. The daily sunlight with the charging current is shown in Figure 5A, which can have the electron mobility within the operation period as shown in Figure 5B. The electron mobility can be changed to the electrical current and found in the Reference 18.

4 | CONCLUSION

The proposed micro-circuit for the thermo-electro-optic energy conversion is a very interesting device that can be

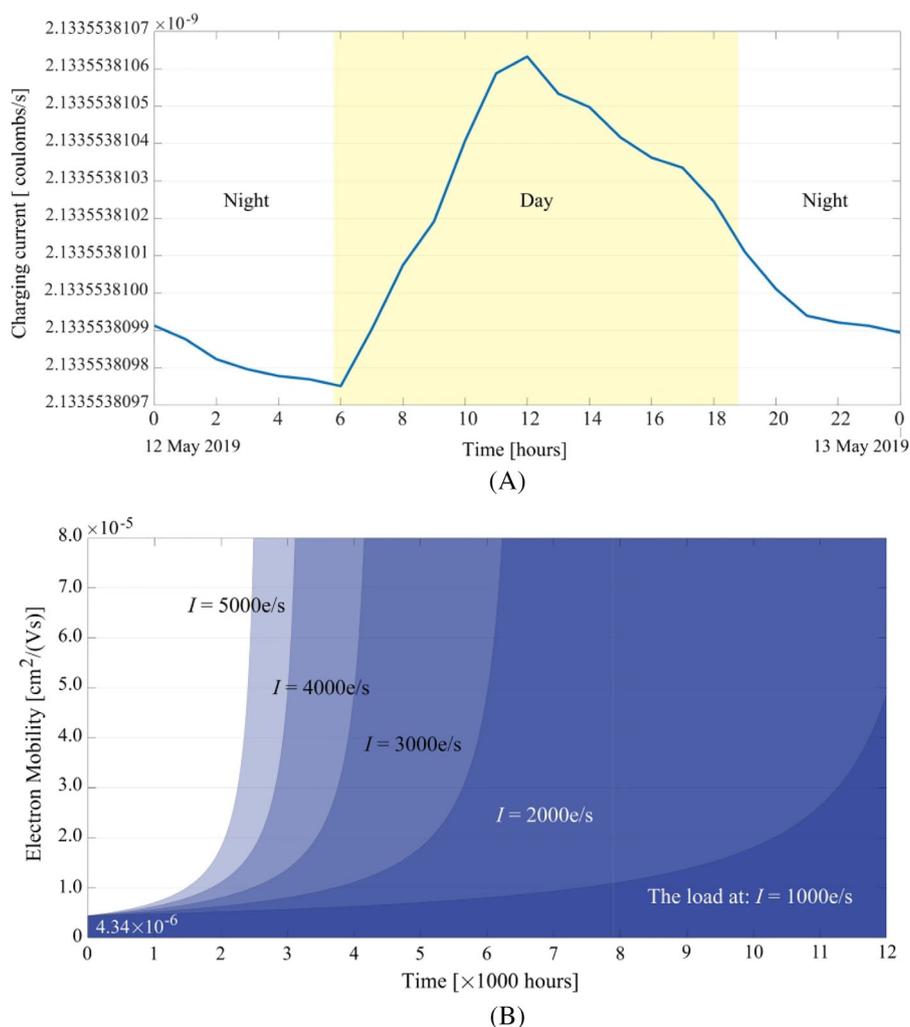


FIGURE 5 In manipulation, the thermal expansion is employed by the relationship between the input light power and the induced electron mobility, where A, the reference to a weather data record,¹⁷ B, the daily charging current for the input light power of 10 mW can be obtained as in the figure, from which the electron mobility of $4.34 \times 10^{-6} \text{ cm}^2 \cdot (\text{V} \cdot \text{s})^{-1}$ can be obtained [Color figure can be viewed at wileyonlinelibrary.com]

practically fabricated and used as one of the selected alternative energy sources. In the manipulation, the significant result of the daily charging electron mobility of $4.34 \times 10^{-6} \text{ cm}^2 \cdot (\text{V} \cdot \text{s})^{-1}$ with the input light power of 10 mW can be obtained. The large area circuits can also be employed to achieve more mobility output for further applications.

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ORCID

Iraj Sadegh Amiri  <https://orcid.org/0000-0001-8121-012X>

Preecha Yupapin  <https://orcid.org/0000-0002-6438-9276>

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